

Schottky Barrier Diode

Features

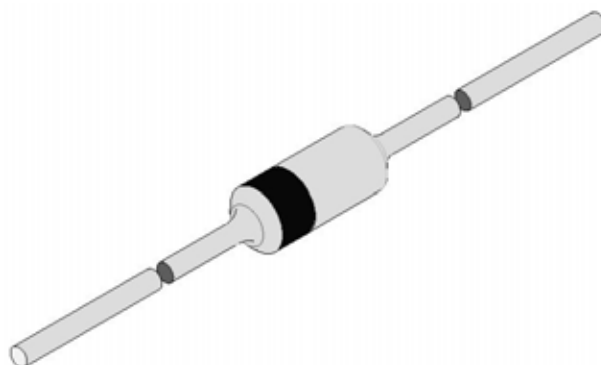
1. High reliability
2. Low reverse current and low forward voltage

Applications

Low current rectification and high speed switching

Construction

Silicon epitaxial planar



Absolute Maximum Ratings

$T_j=25^{\circ}\text{C}$

Parameter	Test Conditions	Type	Symbol	Value	Unit
Repetitive peak reverse voltage		1N60	V_{RRM}	40	V
		1N60P	V_{RRM}	45	V
Peak forward surge current	$t_p \leq 1 \text{ s}$	1N60	I_{FSM}	150	mA
		1N60P	I_{FSM}	500	mA
Forward continuous current	$T_a=25^{\circ}\text{C}$	1N60	I_F	30	mA
		1N60P	I_F	50	mA
Storage temperature range			T_{stg}	-65~+125	$^{\circ}\text{C}$

Maximum Thermal Resistance

$T_j=25^{\circ}\text{C}$

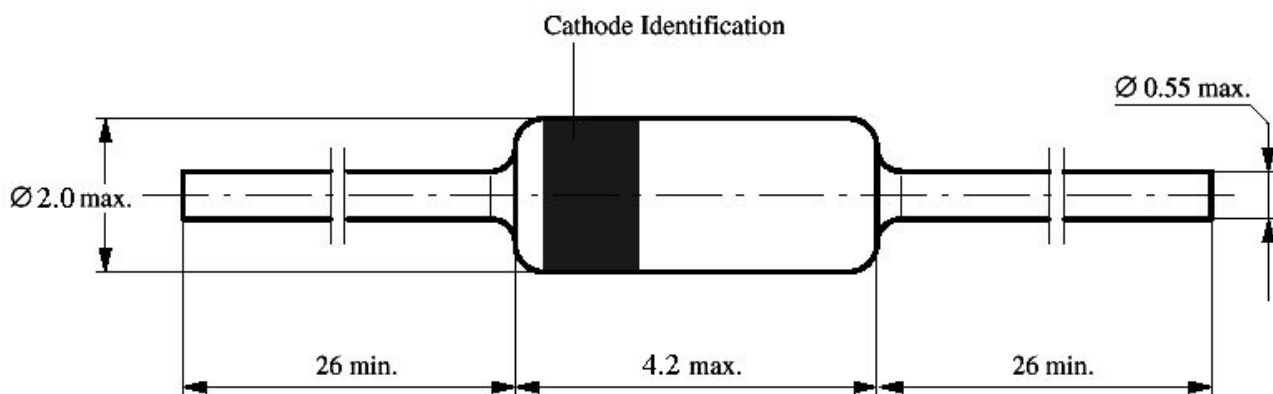
Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	on PC board 50mm × 50mm × 1.6mm	R_{thJA}	250	K/W

Electrical Characteristics

$T_J=25^{\circ}\text{C}$

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=1\text{mA}$	1N60	V_F		0.32	0.5	V
		1N60P	V_F		0.24	0.5	V
	$I_F=30\text{mA}$	1N60	V_F		0.65	1.0	V
		1N60P	V_F		0.65	1.0	V
Reverse current	$V_R=15\text{V}$	1N60	I_R		0.1	0.5	μA
		1N60P	I_R		0.5	1.0	μA
Junction capacitance	$V_R=1\text{V}$, $f=1\text{MHz}$	1N60	C_J		2.0		pF
	$V_R=10\text{V}$, $f=1\text{MHz}$	1N60P	C_J		6.0		pF
Reverse recovery time	$I_F=I_R=1\text{mA}$ $I_{rr}=1\text{mA}$ $R_C=100\Omega$		t_{rr}			1.0	ns

Dimensions in mm



Standard Glass Case
JEDEC DO 35

Formosa MicroSemi CO., LTD.